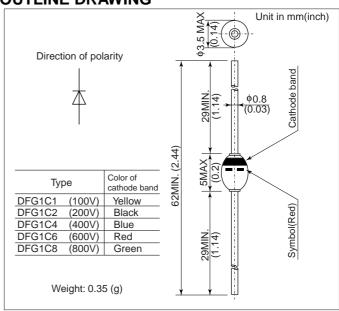
DFG1C

FEATURES

- For high speed switching.
- Diffused-junction. Glass passivated and encapsulated.

OUTLINE DRAWING



ABSOLUTE MAXIMUM RATINGS

Items	Ту	ре	DFG1C1	DFG1C2	DFG1C4	DFG1C6	DFG1C8		
Repetitive Peak Reverse Voltage	V_{RRM}	V	100	200	400	600	800		
Average Forward Current	I _{F(AV)}	А		1.0(TL=80°C	1.0(TL=70°C)				
			(Single-phase half sine wave 180° conduction, Lead length = 10mm)						
Surge(Non-Repetitive) Forward Current	I _{FSM}	А		35	30				
			(Without PIV, 10ms conduction, Tj = 150°C start)						
I ² t Limit Value	l²t	A ² s	4.9			3.6			
			(Time = 2 ~ 10ms, I = RMS value)						
Operating Junction Temperature	T _j	°C	-65 ~ + 150						
Storage Temperature	T _{stg}	°C	-65 ~ +150						

Notes (1) Lead mounting: Lead temperature 300°C max. to 3.2mm from body for 5sec. max..

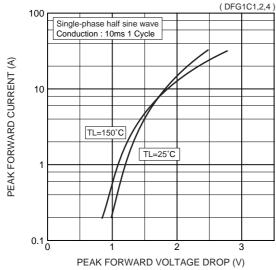
(2) Mechanical strength: Bending 90°×2 cycles or 180°×1 cycle, Tensile 2kg, Twist 90°×1 cycle.

CHARACTERISTICS(T₁=25°C)

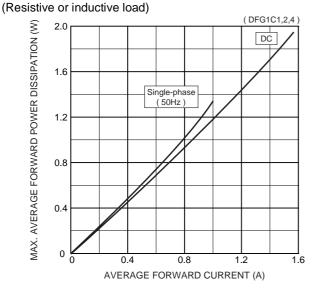
Items	Symbols	Units	Min.	Тур.	Max.	Test Conditions		
Peak Reverse Current	I _{RRM}	μΑ	_	_	10	Rated V _{RRM}		
Peak Forward Voltage	V _{FM}	V	_	_	1.2	DFG1C1,2,4	I _{FM} =1.0Ap, Single-phas	
			_	_	1.6	DFG1C6,8	half sine wave 1 cycle	
Reverse Recovery Time	trr	μs	_	_	0.1	I _F =0.5A, I _{rp} =1.0A, 25% Recovery		
Steady State Thermal Impedance	R _{th(j-a)}	°C/W	_	_	80	Lead length = 10 mm		
					50			

DFG1C

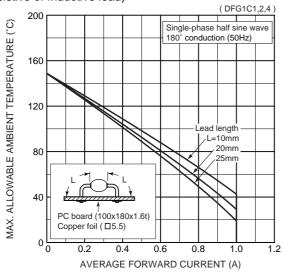
Forward characteristics



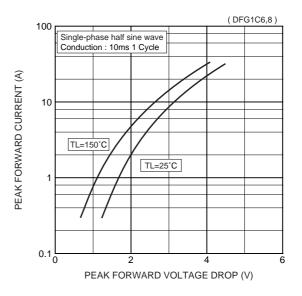
Max. average forward power dissipation



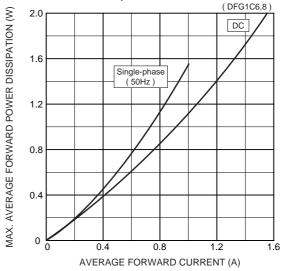
Max. allowable ambient temperature (Resistive or inductive load)



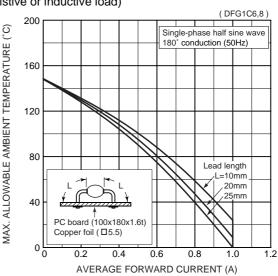
Forward characteristics



Max. average forward power dissipation (Resistive or inductive load)

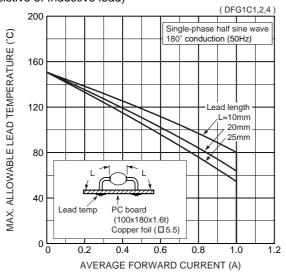


Max. allowable ambient temperature (Resistive or inductive load)

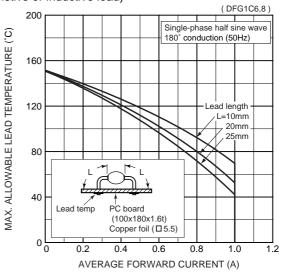


DFG1C

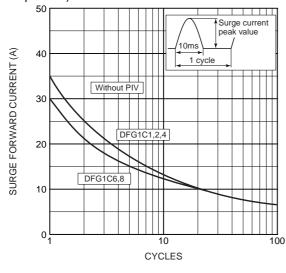
Max. allowable lead temperature (Resistive or inductive load)



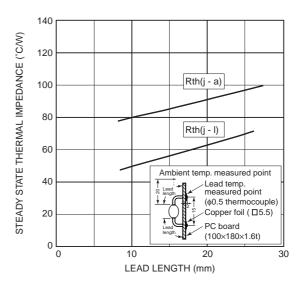
Max. allowable lead temperature (Resistive or inductive load)



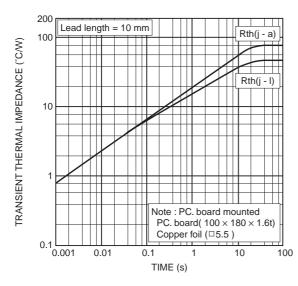
Surge forward current characteristic (Non-repetitive)



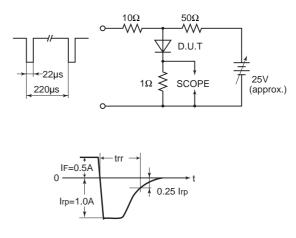
Steady state thermal impedance



Transient thermal impedance



Reverse recovery time (trr) test circuit



HITACHI POWER SEMICONDUCTORS

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